

Features

- Trench LV MOSFET Technology
- High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

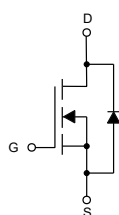
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 120°C/W Junction to Ambient (Note 2)

Parameter	Symbol	Rating	Unit
Drain -Source Voltage	V_{DS}	30	V
Gate -Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	$T_A=25^\circ\text{C}$	A
		$T_A=100^\circ\text{C}$	
Drain Current-Pulsed (Note 3)	I_{DM}	23.2	A
Power Dissipation (Note 4)	P_D	1.04	W

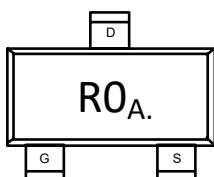
Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

Internal Structure and Marking Code

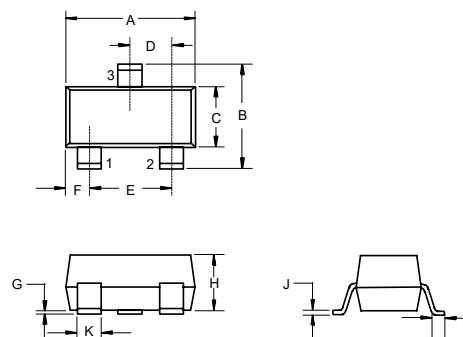


1. GATE
2. SOURCE
3. DRAIN



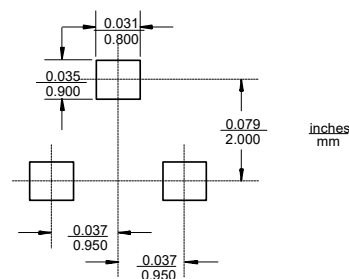
N-Channel MOSFET

SOT-23



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	30			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	0.9	1.4	V
Gate-Body Leakage Current	I _{GSS}	V _{GS} =± 12V, V _{DS} =0V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.8A		20	27	mΩ
		V _{GS} =4.5V, I _D =5A		22	33	
		V _{GS} =2.5V, I _D =4A		27	51	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5A		23		S
Gate Resistance	R _g	f=1 MHz, Open drain		3		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				5.8	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =5.6A			1.2	V
Reverse Recovery Time	t _{rr}	I _F =2.9A, dI _F /dt=300A/μs		14		ns
Reverse Recovery Charge	Q _{rr}			7		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V,f=1MHz		586		pF
Output Capacitance	C _{oss}			57		
Reverse Transfer Capacitance	C _{rss}			48		
Total Gate Charge	Q _g	V _{DS} =15V,V _{GS} =10V,I _D =5.6A		15.3		nC
Gate-Source Charge	Q _{gs}			1.2		
Gate-Drain Charge	Q _{gd}			2.1		
Turn-On Delay Time	t _{d(on)}	V _{DD} =15V,V _{GS} =10V, R _G =2.2Ω, I _D =2.9A		4.1		ns
Turn-On Rise Time	t _r			21		
Turn-Off Delay Time	t _{d(off)}			18		
Turn-Off Fall Time	t _f			1.4		

Curve Characteristics

Fig.1 - Typical Output Characteristics

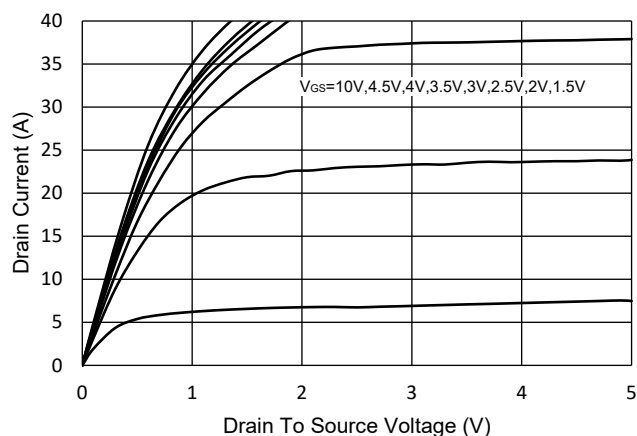


Fig.2 - Transfer Characteristic

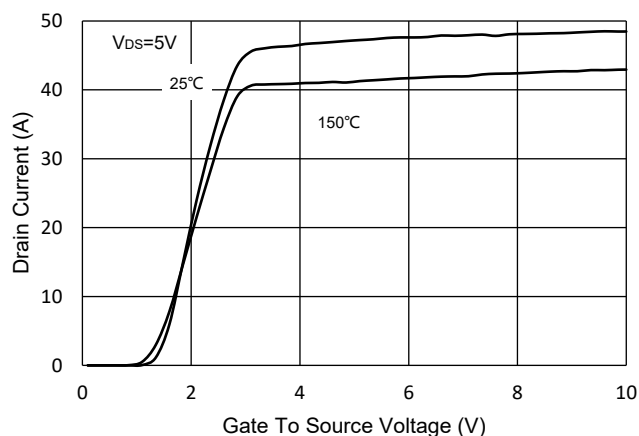


Fig.3 - $R_{DS(ON)}$ - V_{GS}

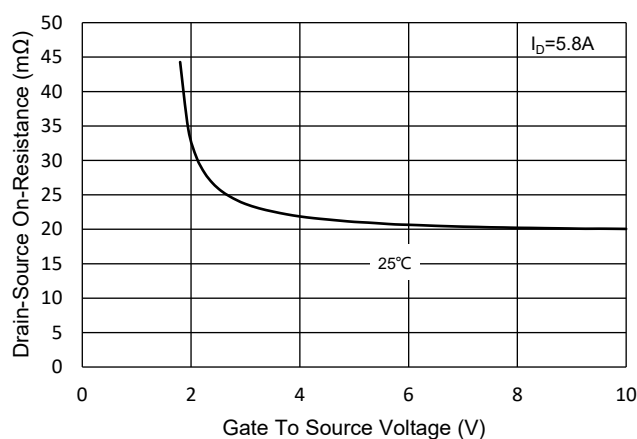


Fig.4 - $R_{DS(ON)}$ - I_D

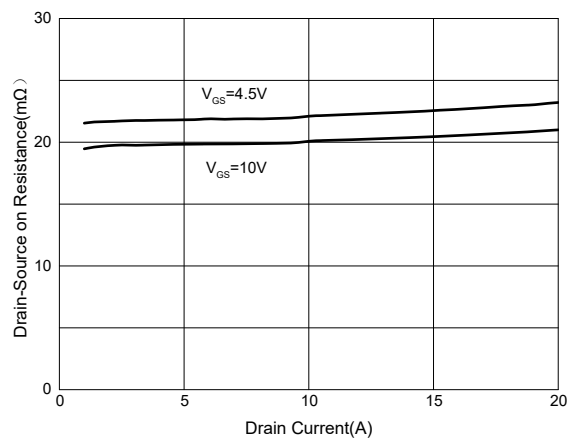


Fig.5 - Capacitance Characteristics

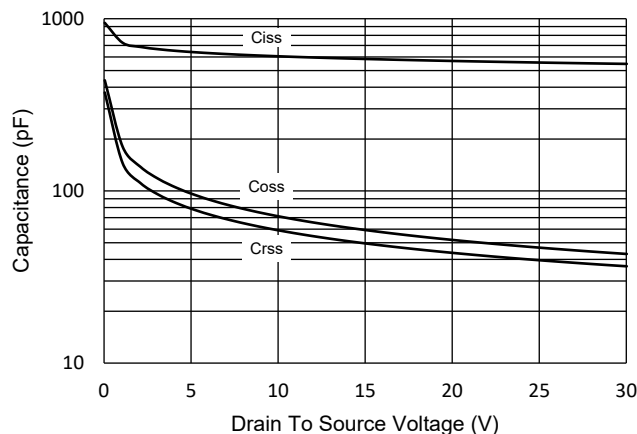
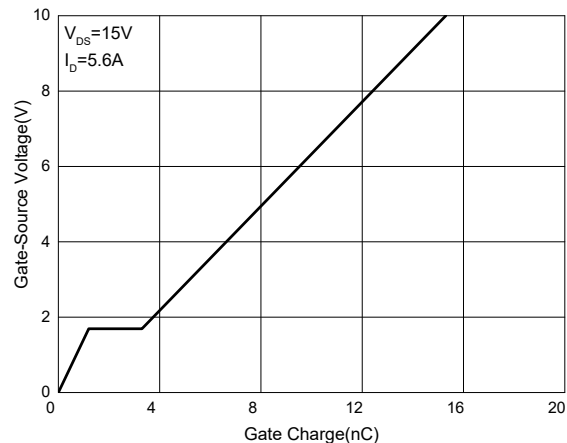


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

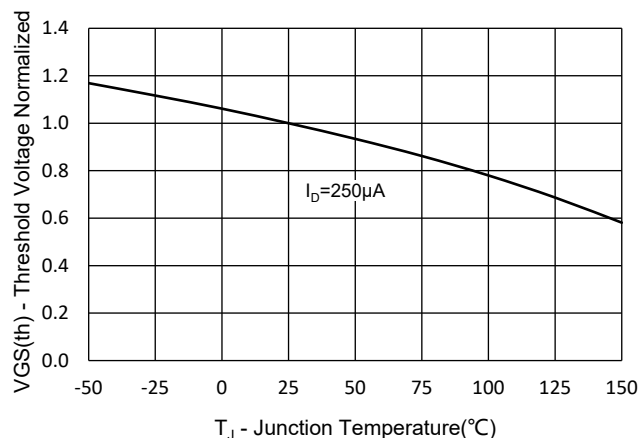


Fig.8 - Normalized On Resistance Characteristics

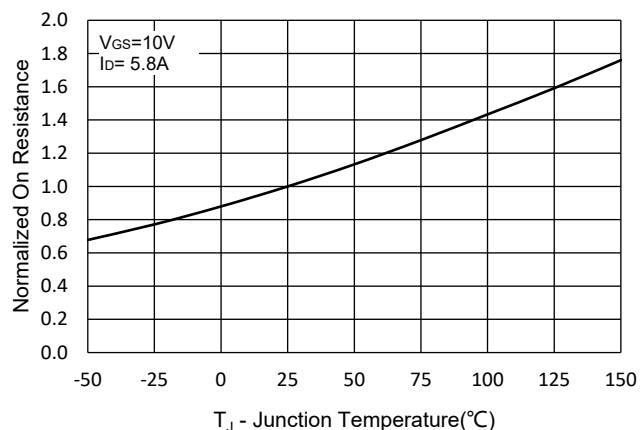


Fig.9 - $I_S - V_{SD}$

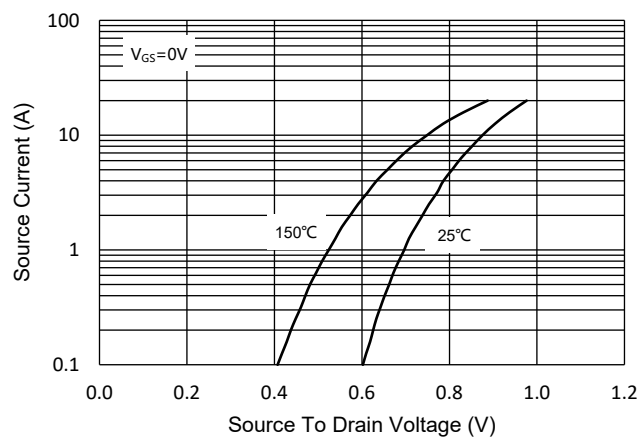


Fig.10 - Drain Current

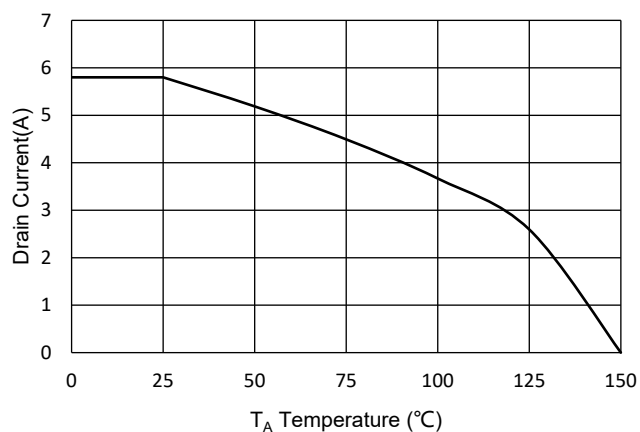
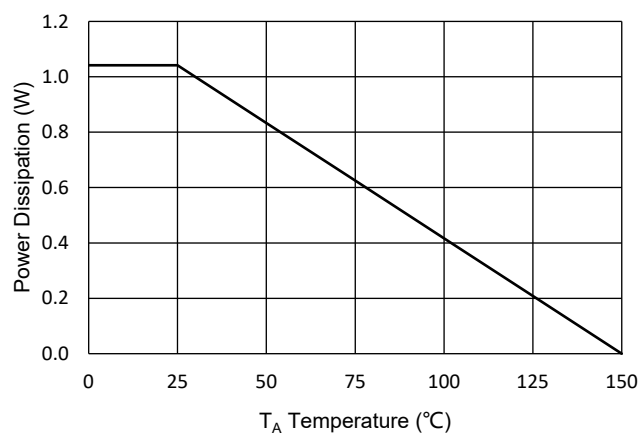


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

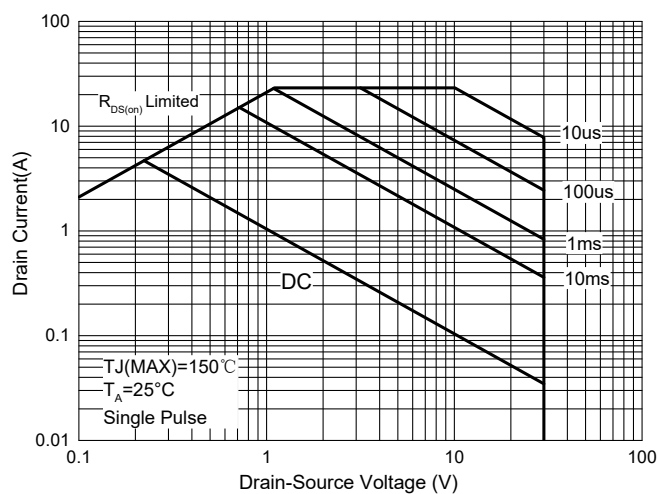
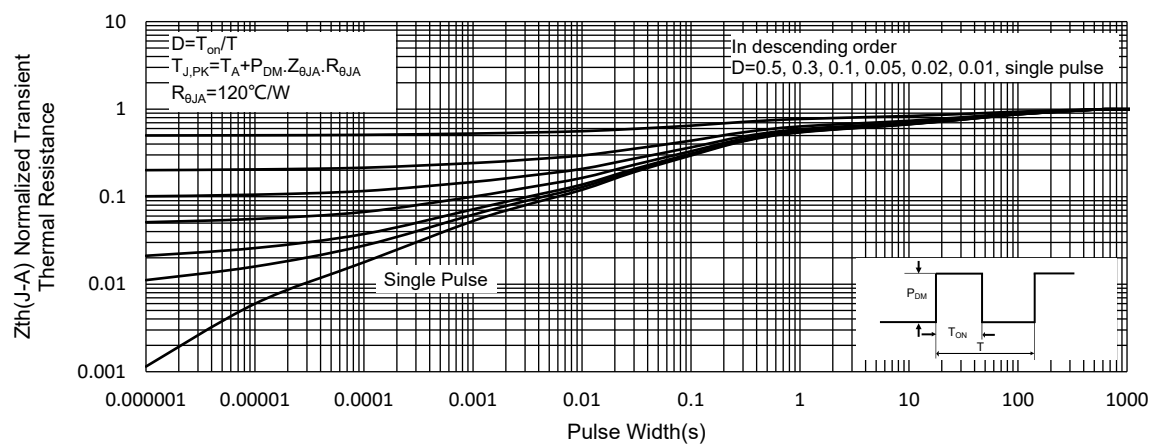


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel

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